

UNISONIC TECHNOLOGIES CO., LTD

UK2158

Preliminary

±0.1A, 50V N-CHANNEL MOSFET FOR HIGH-SPEED SWITCHING

DESCRIPTION

The UTC **UK2158** is an N-channel vertical type MOSFET, it uses UTC's advanced technology to provide customers with high switching speed and low gate cut-off voltage.

The UTC **UK2158** is suitable for use in low-voltage portable systems such as camcorders and headphone stereo sets.

FEATURES

 $\label{eq:RDS(ON)} \begin{array}{l} \leq 50\Omega @ V_{\rm GS} = 1.5V, \ I_{\rm D} = 1.0 mA \\ R_{\rm DS(ON)} \leq 20\Omega @ V_{\rm GS} = 2.5V, \ I_{\rm D} = 10 mA \\ R_{\rm DS(ON)} \leq 15\Omega @ V_{\rm GS} = 4.0V, \ I_{\rm D} = 10 mA \end{array}$

- * High switching speed
- * Low gate cut-off voltage

SYMBOL



ORDERING INFORMATION

Ordering	Daakaga	Pin	Assignm	Deaking			
Lead Free	Halogen Free	Package	1	2	3	Packing	
UK2158L-AE2-R	UK2158G-AE2-R	SOT-23-3	G	S	D	Tape Reel	
Note: Pin Assignment: G:	Gate S: Source D: Dra	in					

UK2158G-AE2-R					
	(1)Packing Type	(1) R: Tape Reel			
	(2)Package Type	(2) AE3: SOT-2			
	(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Fr			

MARKING





ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage (V _{GS} =0)		V _{DSS}	50	V	
Gate-Source Voltage (V _{GS} =0)		V _{GSS}	±7.0	V	
Drain Current	DC	I _{D(DC)}	±0.1	A	
	Pulse (PW≤10ms, Duty Cycle≤50%)	I _{D(PULSE)}	±0.2	А	
Power Dissipation		PD	200	mW	
Channel Temperature		Тсн	+150	°C	
Storage Temperature Range		T _{STG}	-55 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS M		TYP	MAX	UNIT
OFF CHARACTERISTICS					÷.		
Drain-Source Leakage Current		I _{DSS}	V _{DS} =50V, V _{GS} =0V			1.0	μA
Gate-Source Leakage Current	Forward	I	V _{GS} =+7.0V, V _{DS} =0V			+3.0	μA
	Reverse	IGSS	V _{GS} =-7.0V, V _{DS} =0V			-3.0	μA
ON CHARACTERISTICS							
Gate Cut-off Voltage		$V_{GS(OFF)}$	V _{DS} =3V, I _D =1.0µA		0.7	1.1	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =1.5V, I _D =1.0mA		32	50	Ω
			V _{GS} =2.5V, I _D =10mA		16	20	Ω
			V _{GS} =4.0V, I _D =10mA		12	15	Ω
Forward Transfer Admittance		y fs	V _{DS} =3V, I _D =10mA				mS
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}			6		рF
Output Capacitance		Coss	V _{GS} =0V, V _{DS} =3V, f=1.0MHz		8		рF
Reverse Transfer Capacitance					1		рF
SWITCHING PARAMETERS							
Turn-ON Delay Time		t _{D(ON)}			9		ns
Rise Time		t _R	V_{DD} =3V, $V_{GS(ON)}$ =3V, I_D =20mA, R_G =10 Ω , R_L =150 Ω		48		ns
Turn-OFF Delay Time		t _{D(OFF)}			21		ns
Fall-Time		t _F			31		ns



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